

In the Claims:

1. (Currently Amended) A method of manufacturing a module, the method comprising:
providing a ~~device~~ semiconductor wafer that includes a connection area extending over a top surface of the ~~device~~ semiconductor wafer, wherein the connection area comprises a compliant 3D structure that includes a conductor overlying a compliant base element, the conductor being integral with a redistribution layer that overlies the ~~device~~ semiconductor wafer;

applying a casting compound over the top surface of the ~~device~~ semiconductor wafer;
after applying a casting compound, reducing a thickness of the casting compound so that the connection area protrudes through the casting compound;

after applying the casting compound, exposing separation corridors on the semiconductor wafer by removing portions of the casting compound; and

after exposing separation corridors, separating the wafer into a plurality of individual chips.

2. (Currently Amended) The method of claim 1, further comprising, after applying the casting compound, mounting the module to a printed circuit board.

3. (Currently Amended) The method of claim 1, further comprising, after forming the casting compound, attaching the module to a lead frame.

4. (Currently Amended) The method of claim 26, wherein electrically coupling the connection area comprises soldering the connection area to the terminal.

5-9. (Canceled)

10. (Currently Amended) The method of claim [[9]]1, wherein the separation corridors are exposed by a photolithographic process.
11. (Currently Amended) The method of claim [[9]]1, wherein the separation corridors are exposed with use of a laser beam.
12. (Currently Amended) The method of claim [[8]]1, wherein the casting compound is cooled before separating the wafer into a plurality of individual chips.
13. (Currently Amended) The method of claim 1, wherein the casting compound is applied uniformly by spraying, dispensing or printing.
14. (Currently Amended) The method of claim 1, wherein the casting compound has thermal and mechanical properties comparable to those of silicon.
15. (Currently Amended) The method of claim 14, wherein the casting compound comprises a silicon-based material.
16. (Currently Amended) The method of claim 14, wherein the casting compound comprises a thermoplastic material.
17. (Currently Amended) The method of claim 14, wherein the casting compound comprises an epoxy resin.
18. (Canceled)

19. (Currently Amended) The method of claim 1, wherein the thickness of the casting compound is reduced by thermal removal.
20. (Currently Amended) The method of claim 1, wherein the thickness of the casting compound is reduced by etching.
21. (Currently Amended) A method for improving the mechanical properties of a BOC module arrangement in which chips have 3D structures which are mechanically and electrically connected by means of solder connections to terminal contacts on a printed circuit board or leadframe, the method characterized in that a casting compound is applied over a top surface of a semiconductor wafer ~~the chips~~, and excess thickness of the casting compound is removed, in such a way that tips of the 3D structures protrude from the compound, wherein the 3D structures comprise compliant 3D structures each of which includes a conductor overlying a compliant base element, the conductor being integral with a redistribution layer that overlies the top surface of the ~~chips~~ semiconductor wafer, and wherein the after the casting compound is applied, exposing separation corridors by removing portions of the casting compound, and wherein after the exposing the separation corridors, separating the semiconductor wafer into chips.
22. (Canceled)
23. (Currently Amended) The method of claim 21, wherein the conductor comprises metal.
24. (Canceled)

25. (Currently Amended) The method of claim 21, wherein the chips comprise individual semiconductor dies.

26. (Previously Presented) The method of claim 1, further comprising, after applying a casting compound, electrically coupling the connection area to a terminal of a second apparatus.

27. (Currently Amended) The method of claim [[8]]1, wherein separating the wafer into a plurality of individual chips comprises using a laser to separate the wafer.